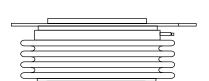


Vishay High Power Products

Phase Control Thyristors (Hockey PUK Version), 560 A



TO-200AC (B-PUK)

560 A

PRODUCT SUMMARY

 $I_{\mathsf{T}(\mathsf{AV})}$

FEATURES

- · Center amplifying gate
- · Metal case with ceramic insulator
- International standard case TO-200AC (B-PUK)



• Designed and qualified for industrial level



ROHS

TYPICAL APPLICATIONS

- DC motor controls
- · Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		560	Α			
I _{T(AV)}	T _{hs}	55	°C			
		1115	A			
I _{T(RMS)}	T _{hs}	25	°C			
1	50 Hz	8000	۸			
I _{TSM}	60 Hz	8380	Α			
124	50 Hz	320	kA ² s			
l ² t	60 Hz	292	KA-S			
V _{DRM} /V _{RRM}		400 to 2000	V			
tq	Typical	100	μѕ			
T _J		- 40 to 125	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$\begin{aligned} I_{DRM}/I_{RRM} & \text{MAXIMUM} \\ \text{AT T}_{J} &= T_{J} & \text{MAXIMUM} \\ \text{mA} \end{aligned}$				
	04	400	500					
	08	800	900					
ST300CL	12	1200	1300	50				
0100002	16	1600	1700	00				
	18	1800	1900					
	20	2000	2100					

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ST300CLPbF Series

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ABSOLUTE MAXIMUM RATIN	GS					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current		180° condu	ction, half sine v	vave	560 (275)	Α
at heatsink temperature	I _{T(AV)}	double side	(single side) co	oled	55 (75)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink tempe	erature double side cooled	1115	
		t = 10 ms	No voltage		8000	
Maximum peak, one-cycle	I	t = 8.3 ms	reapplied		8380	A kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave, initial $T_J = T_J$ maximum	6730	
		t = 8.3 ms	reapplied		7040	
	l ² t	t = 10 ms	No voltage reapplied		320	
Maximum I ² t for fusing		t = 8.3 ms			292	
Maximum i-t for fusing		t = 10 ms			226	
		t = 8.3 ms	reapplied		207	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			3200	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$, $T_J = T_J$ maximum	0.97	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.98	T V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.74	m 0
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$			0.73	mΩ
Maximum on-state voltage	V_{TM}	$I_{pk} = 1635 \text{ A}, T_J = T_J \text{ maximum}, t_p = 10 \text{ ms sine pulse}$			2.18	V
Maximum holding current	I _H	T 05 00 and a sound 40 V and the lead		600	mA	
Typical latching current	Ι _L	T _J = 25 °C, anode supply 12 V resistive load			1000	IIIA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 Ω , $t_r \le 1~\mu s$ $T_J = T_J$ maximum, anode voltage $\le 80~\%~V_{DRM}$	1000	A/µs		
Typical delay time	t _d	Gate current 1 A, $dl_g/dt = 1$ A/ μ s $V_d = 0.67 \% V_{DRM}$, $T_J = 25 °C$	1.0			
Typical turn-off time	tq	$I_{TM} = 550 \text{ A, } T_J = T_J \text{ maximum, dl/dt} = 40 \text{ A/}\mu\text{s,}$ $V_R = 50 \text{ V, dV/dt} = 20 \text{ V/}\mu\text{s, gate 0 V } 100 \Omega, t_p = 500 \mu\text{s}$	100	μs		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs		
Maximum peak reverse and off-state leakage current	I _{RRM,} I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	50	mA		





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TRIGGERING						
DADAMETER	CVMDOL	TEST COMPITIONS		VALUES		што
PARAMETER	SYMBOL	l Es	ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	10.0		w
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50	2	.0	VV
Maximum peak positive gate current	I _{GM}	$T_J = T_J$ maximum,	$t_p \leq 5 \ ms$	3.	.0	Α
Maximum peak positive gate voltage	+ V _{GM}	T - T maximum	+ < 5 ma	20		V
Maximum peak negative gate voltage	- V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms			.0]
		T _J = - 40 °C	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units	200	-	mA
DC gate current required to trigger	I _{GT}	T _J = 25 °C		100	200	
		T _J = 125 °C		50	-	
		T _J = - 40 °C		2.5	-	
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C	12 V anode to cathode applied	1.8	3.0	٧
		T _J = 125 °C		1.1	-]
DC gate current not to trigger	I _{GD}	T T maximum	Maximum gate current/ voltage not to trigger is the maximum value which will not	10.0		mA
DC gate voltage not to trigger	V_{GD}	$T_J = T_J$ maximum	trigger any unit with rated V _{DRM} anode to cathode applied	0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum operating junction temperature range	T_J		- 40 to 125	- °C		
Maximum storage temperature range	T _{Stg}		- 40 to 150			
Maximum thermal resistance, junction to heatsink	D	DC operation single side cooled				
waximum thermal resistance, junction to heatslik	R _{thJ-hs}	DC operation double side cooled	0.05	K/W		
Maximum thermal resistance, case to heatsink	R _{thC-hs}	DC operation single side cooled	0.011	IVVV		
waximum thermal resistance, case to heatslink		DC operation double side cooled	0.006] !		
Mounting force, ± 10 %			9800 (1000)	N (kg)		
Approximate weight			250	g		
Case style		See dimensions - link at the end of datasheet	TO-200AC (B-PUK)		

△R _{thJ-hs} CONDUCTION							
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS	
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS	
180°	0.012	0.010	0.008	0.008		K/W	
120°	0.014	0.015	0.014	0.014	T _J = T _J maximum		
90°	0.018	0.018	0.019	0.019			
60°	0.026	0.027	0.027	0.028			
30°	0.045	0.046	0.046	0.046			

Note

• The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

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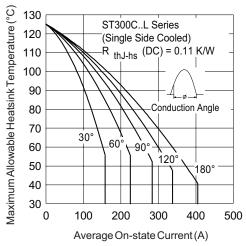


Fig. 1 - Current Ratings Characteristics

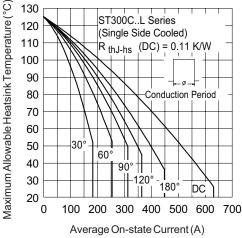


Fig. 2 - Current Ratings Characteristics

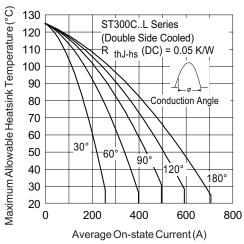


Fig. 3 - Current Ratings Characteristics

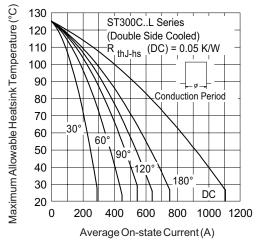


Fig. 4 - Current Ratings Characteristics

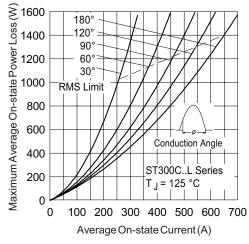


Fig. 5 - On-State Power Loss Characteristics

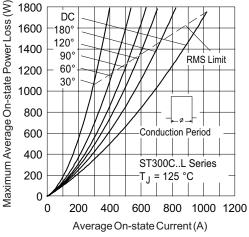


Fig. 6 - On-State Power Loss Characteristics



Phase Control Thyristors Vishay High Power Products (Hockey PUK Version), 560 A

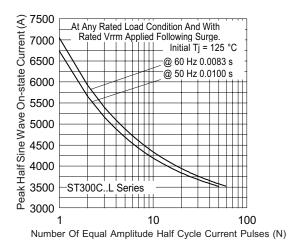


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

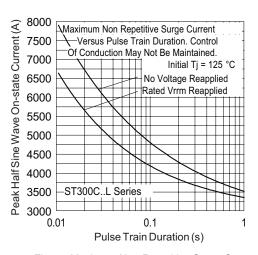


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

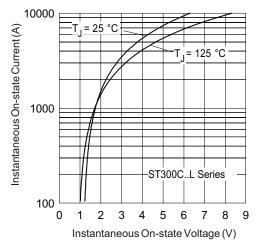


Fig. 9 - On-State Voltage Drop Characteristcs

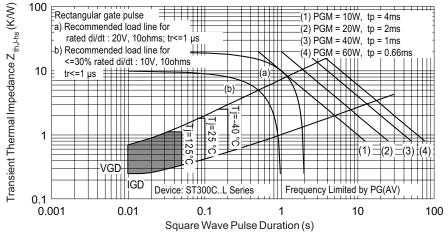


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

Vishay High Power Products Phase Control Thyristors (Hockey PUK Version), 560 A



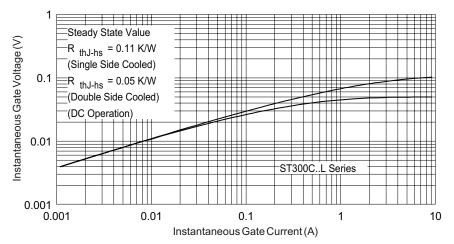
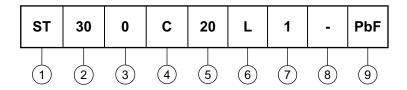


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



- 1 Thyristor
- 2 Essential part number
- 3 0 = Converter grade
- 4 C = Ceramic PUK
- 5 Voltage code x 100 = V_{RRM} (see Voltage Ratings table)
- 6 L = PUK case TO-200AC (B-PUK)
- 7 0 = Eyelet terminals (gate and auxiliary cathode unsoldered leads)
 - 1 = Fast-on terminals (gate and auxiliary cathode unsoldered leads)
 - 2 = Eyelet terminals (gate and auxiliary cathode soldered leads)
 - 3 = Fast-on terminals (gate and auxiliary cathode soldered leads)
- 8 Critical dV/dt: None = 500 V/µs (standard selection)
 - L = 1000 V/µs (special selection)
- 9 Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95076				

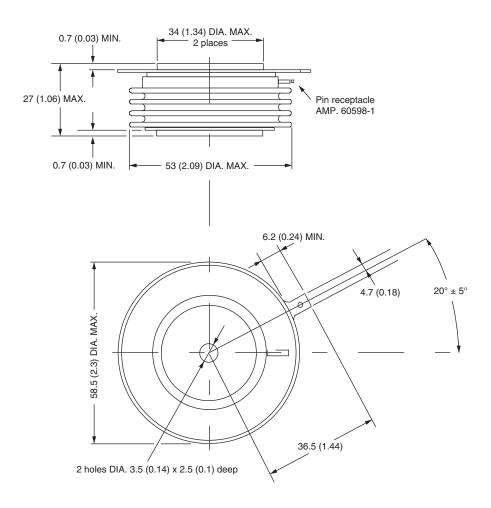


Vishay Semiconductors

TO-200AC (B-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 36.33 (1.430) minimum Strike distance: 17.43 (0.686) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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